

## Wednesday, March 08, 2017

**Registration**      **open from 10:00**

**Opening Ceremony**    **13:00 - 13:30**

Session 1 Silicon I	13:30 - 15:00	Title	Speaker
	13:30 - 14:00	Si epitaxy for power semiconductors	<b>M. Künle</b> (invited) <b>Infineon</b>
	14:00 - 14:20	Coherent, highly-mismatched SiGe/Si-micro-crystals	F. Isa ETH
	14:20 - 14:40	Analysis of Grain Size Homogeneity in High Performance Multicrystalline Silicon	T. Strauch Fraunhofer ISE
	14:40 - 15:00	Influence of the silicon nitride coating on the material quality of directionally solidified multi-crystalline silicon ingots	S. Schwanke Fraunhofer IISB

**Coffee Break**      **15:00 - 15:30**

Session 2 Silicon II	15:30 - 17:10	Title	Speaker
	15:30 - 15:50	Industrial scale Float Zone growth of Silicon single crystals	G. Meisterernst Siltronic
	15:50 - 16:10	Increase the yield of single crystal material for Si-solar cells by detecting the onset of spiral growth during Cz-crystal pulling?	D. Schwabe JLU Giessen
	16:10 - 16:30	Modellierung industrieller Cz-Prozesse für die Photovoltaik	J. Seebeck Fraunhofer IISB
	16:30 - 16:50	Recent Advances in Monocrystalline Ingot Growth by Czochralski using Multipulling	P. Dold Fraunhofer CSP
	16:50 - 17:10	Industrial growth of large silicon crystals	W. Heuwieser Siltronic

**Coffee Break**      **17:10 - 17:30**

Session 3 Awards of the DGKK	17:30 - 18:40	Title
	17:30 - 18:05	<b>Young researcher award of DGKK</b>
	18:05 - 18:40	<b>DGKK award</b>

**General Assembly  
of the DGKK**      **19:00**

## Thursday, March 09, 2017

Session 4 Characterization and Fundamentals	09:00 - 10:10	Title	Speaker
	09:00 - 09:30	<b>Protein Crystallisation: Life in a Lattice</b>	<b>M. Marsh (invited) PSI</b>
	09:30 - 09:50	Evaluation of stress generated by a dislocation wall	D. Berkov General Numerics
	09:50 - 10:10	NaClO <sub>3</sub> Crystal growth in Confinement	F. Kohler Uni Oslo

**Coffee Break      10:10 - 10:40**

Session 5 Novel Materials	10:40 - 12:50	Title	Speaker
	10:40 - 11:10	<b>Growth and Characterization of Geometrically Frustrated Strongly Correlated Electron Systems</b>	<b>V. Fritsch (invited) Uni Augsburg</b>
	11:10 - 11:30	Growing Skyrmionic Cu <sub>2</sub> OSeO <sub>3</sub> Crystals: From Macro to Nanostructures	A. Magrez EPFL
	11:30 - 11:50	Phase transition and new structures at low temperature in Ba <sub>1-x</sub> Sr <sub>x</sub> CuSi <sub>2</sub> O <sub>6</sub> spin dimer compounds	N. van Well PSI
	11:50 - 12:10	YbNi <sub>4</sub> (P <sub>1-x</sub> As <sub>x</sub> ): Single crystal growth and characterization	K. Kliemt Uni Frankfurt
	12:10 - 12:30	Crystal growth of contemporary functional and superconducting materials	N. Zhigadlo Uni Bern
	12:30 - 12:50	Single crystal growth of FeGa <sub>3-x</sub> Ge <sub>x</sub> by Czochralski method	K. Bader LMU München

**Lunch Break      12:50 - 14:30**

**Poster Session      14:30 - 16:00**

Session 6 Oxide Materials	16:00 - 17:50	Title	Speaker
	16:00 - 16:30	<b>Yb:CAIGO and other crystals for ultrashort pulse lasers</b>	<b>C. Liebald (invited) FEE</b>
	16:30 - 16:50	Numerical modelling of the bulk growth of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> single crystals by the Czochralski method	K Böttcher IKZ
	16:50 - 17:10	High oxygen pressure synthesis and crystal growth of transition metal complex oxides	E. Pomjakushina PSI
	17:10 - 17:30	Single crystal growth of Li <sub>2</sub> IR <sub>2</sub> O <sub>3</sub> from separated educts	A. Jesche Uni Augsburg

	17:30 - 17:50	Growth and optical properties of SrTiO <sub>3</sub> and Tb <sub>2</sub> Ti <sub>2</sub> O <sub>7</sub> bulk crystals	D. Kok IKZ
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**Break 17:50 - 19:00**

## Friday, March 10, 2017

Session 7 Epitaxy I	08:30 - 10:30	Title	Speaker
	08:30 - 09:00	<b>HVPE-GaN-crystal growth on foreign substrates</b>	<b>B. Weinert (invited)</b> FCM
	09:00 - 09:20	Growth of GaN layers by high-temperature vapor phase epitaxy	T. Schneider TUBA
	09:20 - 09:40	Growth and Characterization of Buffer Structures for AlGaN/GaN-based Heterostructure Field Effect Transistors	M. Heuken AIXTRON SE
	09:40 - 10:00	Status of AlN Bulk Crystal Growth for Use as Substrates in Deep-UV Applications	M. Bickermann IKZ
	10:00 - 10:30	<b>Efficiency of blue light emitting diodes: the role of InGaN alloy atomic disorder</b>	<b>N. Grandjean (invited)</b> EPFL

**Coffee Break 10:30 - 11:00**

Session 8 Epitaxy II	11:00 - 12:50	Title	Speaker
	11:00 - 11:30	<b>Defects in synthetic diamond and homoepitaxial diamond layers</b>	<b>V. Cimalla (invited)</b> Fraunhofer IAF
	11:30 - 11:50	In situ removal of a native oxide layer on silicon substrates by UV-laser for epitaxial applications	C. Ehlers IKZ
	11:50 - 12:10	Influence of post-epi processing on point defects in 4H-SiC	J. Erlekampf Fraunhofer IISB
	12:10 - 12:30	Controlling the growth direction of self-catalyzed InAs nanowires	H. Potts EPFL
	12:30 - 12:50	Improving the Cost Effectiveness of III-V Materials	R. Lang Fraunhofer ISE

**Closing Ceremony 12:50 - 13:00**

**Lab Tour at Fraunhofer ISE 15:00 - 17:00 optional**